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MAIN REQUEST

CLAIMS

- 1. Apparatus for selectively interfering with pathological cells survival processes in vitro and in vivo comprising:
- means for denerating static magnetic (S) fields crossing a working environment,
- means for gamerating electromagnetic extremely low frequency (ELF) fields over said working environment in addition to said S fields;

characterised in that it further comprises:

- means for modulating said S fields associated to said means for generating S fields, said means for modulating said S fields setting the intensity of said S fields between 1 and 100 mT according to a predetermined function of intensity versus time;
 - means for modulating said ELF fields associated to said means for generating ELF fields, said means for modulating, said ELF fields setting said ELF fields according to a predetermined function of amplitude of intensity between 1 and 100 mT and frequency between 1 and 1000 Hz versus time.
 - 2. Apparatus for selectively interfering with pathological cells survival processes in vitro and in vivo comprising:
 - means for generating static magnetic (S) fields crossing a working environment,

characterised in that it further comprises

- means for modulating said S fields associated to said generating means, said means for modulating the S fields setting the intensity of said S fields between 1 and 100 mT according to a predetermined function of intensity versus time.

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- 3. Apparatus for selectively interfering with pathological cells survival processes in vitro and in vivo characterised in that it further comprises
- means for generating electromagnetic extremely low frequency (ELF) fields over said working environment;
 - means for modulating said ELF fields associated to said means for generating said means for modulating said ELF fields setting said ELF fields according to a predetermined function of amplitude of intensity between 1 and 100 mT and frequency between 1 and 1000 Hz versus time.
 - 4. Apparatus according to any of claims 1 or 2 wherein said means for modulating said S fields comprises program means that set said intensity following a plurality of predetermined step values Is1, Is2, ..., Isn for corresponding time intervals T1, T2, ..., Tn.
 - 5. Apparatus according to any of claims 1 or 3 wherein said means for modulating said ELF fields comprises program means that set said intensity amplitude following a plurality of predetermined step values Inter, Islam, ..., IELEM for corresponding time intervals T1, T2, ..., Ta.
 - 6. Apparatus according to any of claims 1 or 3 wherein said means for modulating said ELF fields comprises program means that set said frequency following a plurality of predetermined step values f1, f2,..., fn, for corresponding time intervals T1, T2, ..., Tn, said step values being comprised between 10 and 100 Hz.
 - 7. Apparatus according to claim 1, wherein said means for modulating said S and ELF fields comprises program means that set an S/ELF ratio according to a plurality of predetermined step values Isi/Impl. Isi/Impl. Isi/Impl. Isi/Impl. ion corresponding time intervals Ti, Ta, ..., Ta,.
 - 8. Apparatus according to claim 7, wherein said program

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means set said S and ELF fields according to an overall intensity between 1 and 30 mT and respectively a ratio S/ELF comprised between 0,1 and 10.

- 9. Apparatus according to claim 7, wherein said program means set said s and ELF fields according to an overall intensity between 1 and 10 mT and respectively a ratio S/ELF comprised between 0,5 and 5.
 - 10. Apparatus according to claims 4 to 9 wherein said program means set said time intervals between 1 and 40 minutes.
 - 11. Apparatus according to the previous claims wherein at least a portion of said working environment is defined by walls permeable to said fields.
 - 12. Apparatus according to the previous claims, wherein said means for generating said S and/or ELF fields a second and first least a \ comprise at respectively surrounding at least a portion of said working environment, said means for modulating AC DC and/or said coils providing to respectively.
 - 13. Apparatus according to the claims from 1 to 11, wherein said means for generating said S and/or ELF fields comprise at least a first and a second coil coaxial to each other, said working environment being placed between said first and a second coil and said means for modulating providing to said coils DC and/or AC current respectively.
 - 16. Apparatus according to the previous claims, wherein means are provided for creating through said working environment a static electric field or a low frequency variable electric field up to 1000 Hz, having intensity up to 20 kV/m.
 - 15. The use of SELF non thermal field for selectively

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interfering with pathological cells survival, such as in particular cells affected by cancer, viral infections, autoimmune diseases, neurodegenerative disorders, AIDS, etc., characterised in that said SELF non thermal fields have intensity comprised between 1 and 100 mT, said SELF fields being different sequences of S and/or ELF fields, i.e. S fields followed by ELF fields, ELF fields followed by S fields, S and ELF field together, as well as the presence of S or ELF fields alone, said ELF fields having a field frequency comprised between 1 and 1000 Hz.

- fields for thermal SELF' non of use 16. The genes \ modifications, in such biotechnological particular for modification of mutant p53 characterised in that said SELF non thermal fields have intensity comprised between 1 and 100 mT, said SELF fields being different sequences of S and/or ELF fields, i.e. S fields followed by ELF fields, ELF fields followed by S fields, \S and ELF field together, as well as the presence of S or ELF fields alone, said ELF fields having a field frequency comprised between 1 and 1000 Hz.
- 17. The use of SELF non thermal fields according to claims
 15 or 16, wherein chemical substances are used in
 addition to the SELF fields.
- 18. The use of SELF non thermal fields according to claims 15 or 16, wherein said different sequences of S and/or ELF fields sequences are set for time intervals T₁, T₂, ..., T_n, and wherein in said time intervals the intensity of said S and/or ELF fields are set at steady values Is₁, I_{S2}, ..., I_{en}; I_{ELF1}, I_{ELF2}, ..., I
- 19. The use of SELF non thermal fields according to claims

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15 or 16, wherein said S and ELF fields are set at an overall intensity between 1 and 30 mT with respectively a ratio S/ELF comprised between 0.1 and 10.

20. The use of SELF non thermal fields according to claims 15 or 16, wherein said S and ELF fields are set at an overall intensity between 1 and 10 mT with respectively a ratio S/ELF comprised between 0,5 and 2,5.